Hisashi Masui

List of Publications by Year
in descending order

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44 papers	1,747 citations	304743 22 h-index	289244 40 g-index
44 all docs	44 docs citations	44 times ranked	1283 citing authors

#	Article	IF	Citations
1	Effects of Growth Temperature and Postgrowth Annealing on Inhomogeneous Luminescence Characteristics of Green-Emitting InGaN Films. Journal of Electronic Materials, 2010, 39, 15-20.	2.2	3
2	Nonpolar and Semipolar III-Nitride Light-Emitting Diodes: Achievements and Challenges. IEEE Transactions on Electron Devices, 2010, 57, 88-100.	3.0	230
3	Technique to evaluate the diode ideality factor of light-emitting diodes. Applied Physics Letters, 2010, 96, 073509.	3.3	25
4	Spontaneous formation of lbrace 1,ar{1},0,1brace InGaN quantum wells on a (1,1,ar{2} ,2) GaN template and their electroluminescence characteristics. Semiconductor Science and Technology, 2010, 25, 015003.	2.0	3
5	Customized Filter Cube in Fluorescence Microscope Measurements of InGaN/GaN Quantum-Well Characterization. Japanese Journal of Applied Physics, 2009, 48, 098003.	1.5	1
6	Luminescence Characteristics of N-Polar GaN and InGaN Films Grown by Metal Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2009, 48, 071003.	1.5	31
7	Effects of piezoelectric fields on optoelectronic properties of InGaN/GaN quantum-well light-emitting diodes prepared on nonpolar (1â€‰0â€‰ ar1 â€‰0) and semipolar (1â€‰1â€‰ ar{2} â€‰2) orientations. Journal Physics D: Applied Physics, 2009, 42, 135106.	2.8	49
8	Geometrical Characteristics and Surface Polarity of Inclined Crystallographic Planes of the Wurtzite and Zincblende Structures. Journal of Electronic Materials, 2009, 38, 756-760.	2.2	21
9	Recent progress in nonpolar LEDs as polarized light emitters. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 203-205.	1.8	9
10	Highly efficient broadâ€area blue and white lightâ€emitting diodes on bulk GaN substrates. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 200-202.	1.8	29
11	Enhancement of external quantum efficiency in GaNâ€based light emitting diodes using a suspended geometry. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2216-2218.	0.8	8
12	Optical polarization of m â€plane Inâ€GaN/GaN lightâ€emitting diodes characterized via confocal microscope. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1203-1206.	1.8	25
13	Effects of off-axis GaN substrates on optical properties of m-plane InGaN/GaN light-emitting diodes. Journal of Crystal Growth, 2008, 310, 4968-4971.	1.5	25
14	Comparison of InGaN/GaN light emitting diodes grown on m â€plane and a â€plane bulk GaN substrates. Physica Status Solidi - Rapid Research Letters, 2008, 2, 89-91.	2.4	46
15	Optical properties of yellow light-emitting diodes grown on semipolar (112Â¯2) bulk GaN substrates. Applied Physics Letters, 2008, 92, .	3.3	167
16	Optical polarization characteristics ofm-oriented InGaN/GaN light-emitting diodes with various indium compositions in single-quantum-well structure. Journal Physics D: Applied Physics, 2008, 41, 225104.	2.8	57
17	Analytical light-ray tracing in two-dimensional objects for light-extraction problems in light-emitting diodes. Applied Optics, 2008, 47, 88.	2.1	10
18	Nonâ€polarâ€oriented InGaN lightâ€emitting diodes for liquidâ€crystalâ€display backlighting. Journal of the Society for Information Display, 2008, 16, 571-578.	2.1	25

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19	Increased Polarization Ratio on Semipolar (1122) InGaN/GaN Light-Emitting Diodes with Increasing Indium Composition. Japanese Journal of Applied Physics, 2008, 47, 7854.	1.5	28
20	Equivalent-Circuit Analysis for the Electroluminescence-Efficiency Problem of InGaN/GaN Light-Emitting Diodes. Japanese Journal of Applied Physics, 2008, 47, 2112.	1.5	11
21	Quantum-confined Stark effect on photoluminescence and electroluminescence characteristics of InGaN-based light-emitting diodes. Journal Physics D: Applied Physics, 2008, 41, 165105.	2.8	55
22	Experimental technique to correlate optical excitation intensities with electrical excitation intensities for semiconductor optoelectronic device characterization. Semiconductor Science and Technology, 2008, 23, 085018.	2.0	11
23	A yellow-emitting Ce3+ phosphor, La1âˆ'xCexSr2AlO5, for white light-emitting diodes. Applied Physics Letters, 2008, 93, .	3.3	158
24	Optical polarization characteristics of InGaNâ•GaN light-emitting diodes fabricated on GaN substrates oriented between (101Â¯) and (101Â¯1Â¯) planes. Applied Physics Letters, 2008, 92, .	3.3	34
25	Optical polarization characteristics of light emission from sidewalls of primary-color light-emitting diodes. Semiconductor Science and Technology, 2008, 23, 072001.	2.0	13
26	Electroluminescence efficiency of (1,0,ar{1},0) -oriented InGaN-based light-emitting diodes at low temperature. Journal Physics D: Applied Physics, 2008, 41, 082001.	2.8	18
27	63.4: Invited Paper: Development and Application Prospects of InGaNâ€based Optoelectronic Devices Prepared in Nonpolar Orientations. Digest of Technical Papers SID International Symposium, 2008, 39, 969-971.	0.3	0
28	Photoelectrochemical Properties of Nonpolar and Semipolar GaN. Japanese Journal of Applied Physics, 2007, 46, 6573-6578.	1.5	27
29	Electrical Characteristics of Nonpolar InGaN-Based Light-Emitting Diodes Evaluated at Low Temperature. Japanese Journal of Applied Physics, 2007, 46, 7309.	1.5	4
30	Radiative Recombination Efficiency of InGaN-Based Light-Emitting Diodes Evaluated at Various Temperatures and Injection Currents. Japanese Journal of Applied Physics, 2007, 46, L627-L629.	1.5	9
31	Direct evaluation of reflector effects on radiant flux from InGaN-based light-emitting diodes. Applied Optics, 2007, 46, 5974.	2.1	15
32	High Power and High External Efficiencym-Plane InGaN Light Emitting Diodes. Japanese Journal of Applied Physics, 2007, 46, L126-L128.	1.5	241
33	Hexagonal pyramid shaped light-emitting diodes based on ZnO and GaN direct wafer bonding. Applied Physics Letters, 2006, 89, 171116.	3.3	32
34	Optimized doping and contact scheme for low-voltage 275-nm deep ultraviolet LEDs. Journal of Electronic Materials, 2006, 35, 750-753.	2.2	8
35	First-Moment Analysis of Polarized Light Emission from InGaN/GaN Light-Emitting Diodes Prepared on Semipolar Planes. Japanese Journal of Applied Physics, 2006, 45, L904-L906.	1.5	28
36	Electroluminescent and Electrical Characteristics of Polar and Nonpolar InGaN/GaN Light-Emitting Diodes at Low Temperature. Japanese Journal of Applied Physics, 2006, 45, 7661-7666.	1.5	11

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37	Nonpolarm-Plane Blue-Light-Emitting Diode Lamps with Output Power of 23.5 mW under Pulsed Operation. Japanese Journal of Applied Physics, 2006, 45, 739-741.	1.5	68
38	Light-polarization characteristics of electroluminescence from InGaNâ•GaN light-emitting diodes prepared on (1122)-plane GaN. Journal of Applied Physics, 2006, 100, 113109.	2.5	46
39	Polarized Light Emission from Nonpolar InGaN Light-Emitting Diodes Grown on a Bulkm-Plane GaN Substrate. Japanese Journal of Applied Physics, 2005, 44, L1329-L1332.	1.5	68
40	Milliwatt Power Deep Ultraviolet Light Emitting Diodes Grown on Silicon Carbide. Japanese Journal of Applied Physics, 2005, 44, L502-L504.	1.5	23
41	A semipolar (10-1-3) InGaN/GaN green light emitting diode. Materials Research Society Symposia Proceedings, 2005, 892, 418.	0.1	1
42	Nonpolar and Semipolar Orientations: Material Growth and Properties. Materials Science Forum, 0, 590, 211-232.	0.3	3
43	Compositional Dependence of Nonpolarm-Plane In_xGa_{1-x}N/GaN Light Emitting Diodes. Applied Physics Express, 0, 1, 041101.	2.4	53
44	Correlation between Optical Polarization and Luminescence Morphology of (11ar22)-Oriented InGaN/GaN Quantum-Well Structures. Applied Physics Express, 0, 2, 071002.	2.4	27